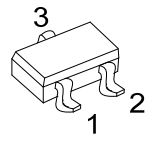
# -4.0A, -100V P-CHANNEL POWER MOSFET




SOT-23
(EIAJ SC-59)

## ■ DESCRIPTION

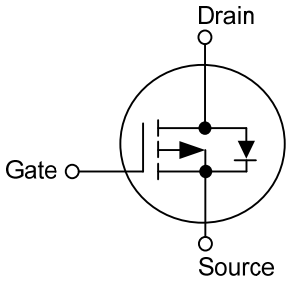
The UTC **UT4P10M** is a P-channel MOS Field Effect Transistor. it uses UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance.

The UTC **UT4P10M** is suitable for high voltage switching applications.

## ■ FEATURES

* $R_{DS(ON)} \leq 500\ m\Omega$ @ $V_{GS}$ = -10V, $I_D$ = -2.0A
  $R_{DS(ON)} \leq 600\ m\Omega$ @ $V_{GS}$ = -4.5V, $I_D$ = -2.0A
* High switching speed
* Low input capacitance

## ■ SYMBOL




## ■ ORDERING INFORMATION

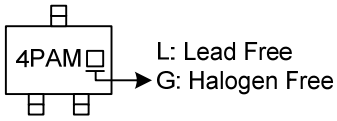
| Ordering Number | | Package | Pin Assignment | | | Packing |
|---|---|---|---|---|---|---|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| UT4P10ML-AE3-R | UT4P10MG-AE3-R | SOT-23 | G | S | D | Tape Reel |

Note: Pin Assignment: G: Gate S: Source D: Drain

UT4P10MG-AE3-R

| | |
|---|---|
| (1)Packing Type | (1) R: Tape Reel |
| (2)Package Type | (2) AE3: SOT-23 |
| (3)Green Package | (3) G: Halogen Free and Lead Free, L: Lead Free |

## ■ MARKING



## ■ ABSOLUTE MAXIMUM RATING ($T_C$=25°C unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DSS}$ | -100 | V |
| Gate-Source Voltage | | $V_{GSS}$ | ±20 | V |
| Drain Current | DC | $I_D$ | -4 | A |
| | Pulsed (Note 2) | $I_{DM}$ | -12 | A |
| Avalanche Energy | Single Pulsed (Note 3) | $E_{AS}$ | 6.7 | mJ |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 3.25 | V/ns |
| Power Dissipation ($T_A$=25°C) | | $P_D$ | 0.3 | W |
| Junction Temperature | | $T_J$ | +150 | °C |
| Storage Temperature Range | | $T_{STG}$ | -55 ~ +150 | °C |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 0.1mH, $I_{AS}$ = -11.6A, $V_{DD}$ = -70V, $R_G$ = 25Ω, Starting $T_J$ = 25°C
4. $I_{SD}$ ≤ -4.0A, di/dt ≤ 200A/μs, $V_{DD}$ ≤ $BV_{DSS}$, Starting $T_J$ = 25°C

## ■ THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---|---|---|---|
| Junction to Ambient | $\theta_{JA}$ | 416 | °C/W |

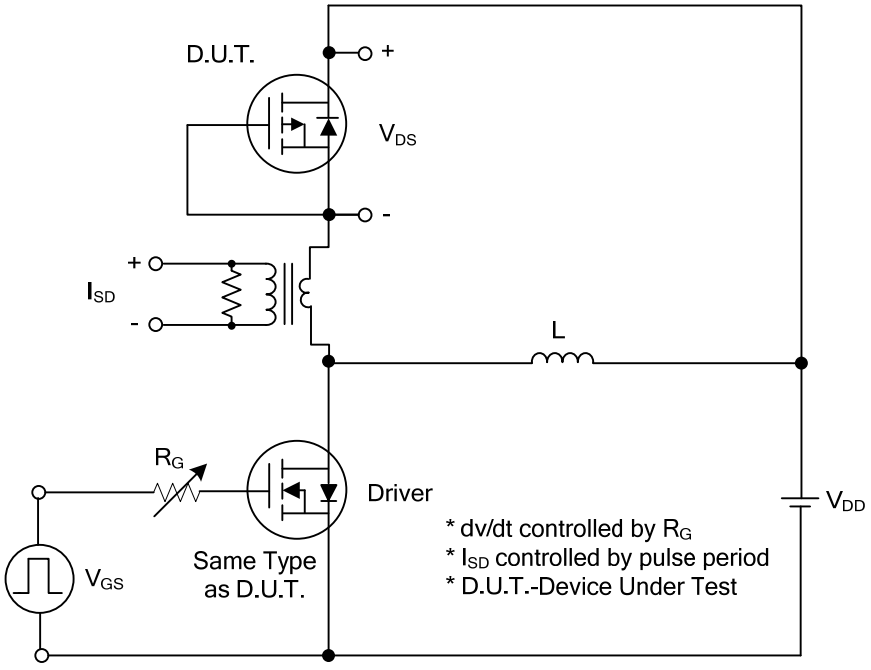
Note: Device mounted on FR-4 substrate $P_C$ board, 2oz copper, with 1inch square copper plate.

## ■ ELECTRICAL CHARACTERISTICS ($T_J$=25°C unless otherwise specified)

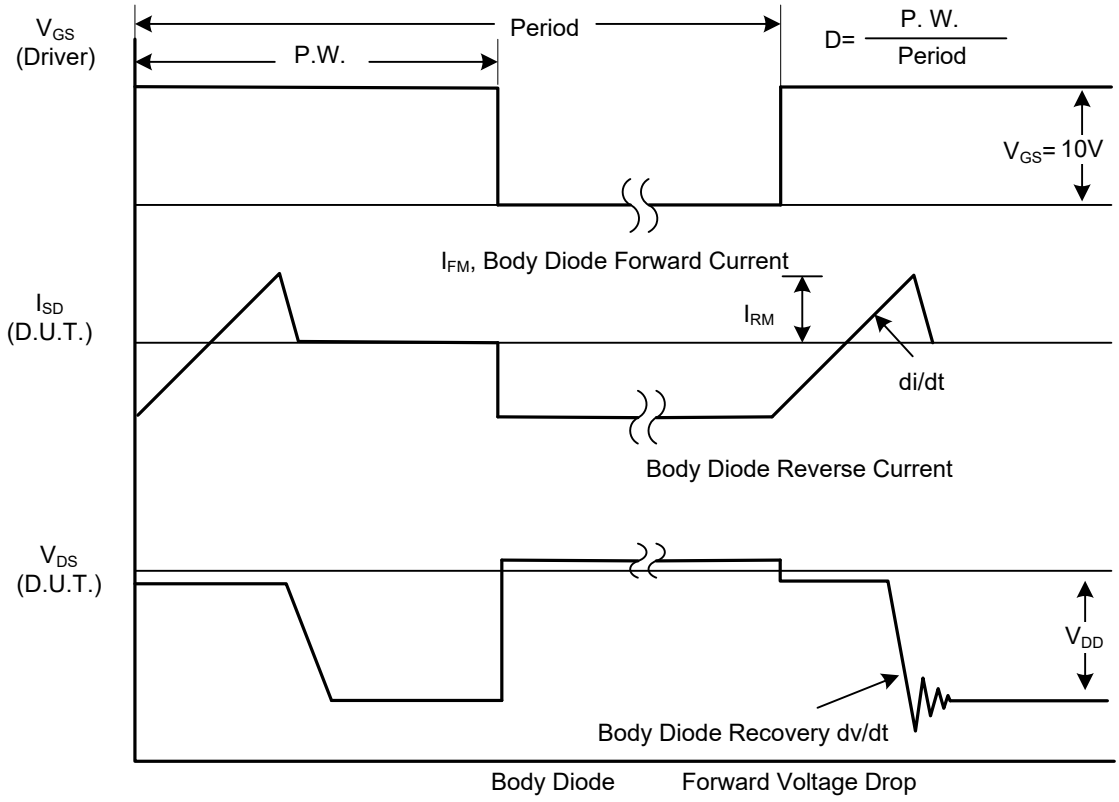
| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain-Source Breakdown Voltage | | $BV_{DSS}$ | $V_{GS}$=0V, $I_D$=-250μA | -100 | | | V |
| Drain-Source Leakage Current | | $I_{DSS}$ | $V_{DS}$=-100V, $V_{GS}$=0V | | | -1 | μA |
| Gate-Source Leakage Current | Forward | $I_{GSS}$ | $V_{GS}$=+20V, $V_{DS}$=0V | | | +100 | nA |
| | Reverse | | $V_{GS}$=-20V, $V_{DS}$=0V | | | -100 | nA |
| **ON CHARACTERISTICS** | | | | | | | |
| Gate Threshold Voltage | | $V_{GS(TH)}$ | $V_{DS}$= $V_{GS}$, $I_D$=-250μA | -1.0 | | -3.0 | V |
| Static Drain-Source On-State Resistance (Note 1, 2) | | $R_{DS(ON)}$ | $V_{GS}$=-10V, $I_D$ =-2.0A | | | 500 | mΩ |
| | | | $V_{GS}$ =-4.5V, $I_D$ =-2.0A | | | 600 | mΩ |
| **DYNAMIC PARAMETERS** | | | | | | | |
| Input Capacitance | | $C_{ISS}$ | $V_{GS}$=0V, $V_{DS}$=-25V, f=1.0MHz | | 680 | | pF |
| Output Capacitance | | $C_{OSS}$ | | | 35 | | pF |
| Reverse Transfer Capacitance | | $C_{RSS}$ | | | 25 | | pF |
| **SWITCHING PARAMETERS** | | | | | | | |
| Total Gate Charge | | $Q_G$ | $V_{DS}$=-80V, $V_{GS}$=-10V, $I_D$=-4.0A, (Note 1, 2) | | 18 | | nC |
| Gate to Source Charge | | $Q_{GS}$ | | | 2 | | nC |
| Gate to Drain Charge | | $Q_{GD}$ | | | 4 | | nC |
| Turn-ON Delay Time | | $t_{D(ON)}$ | $V_{DS}$=-50V, $V_{GS}$=-10V, $I_D$=-4.0A, $R_G$=3Ω (Note 1, 2) | | 6 | | ns |
| Rise Time | | $t_R$ | | | 18 | | ns |
| Turn-OFF Delay Time | | $t_{D(OFF)}$ | | | 19 | | ns |
| Fall-Time | | $t_F$ | | | 19 | | ns |
| **SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS** | | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | | $I_S$ | (Note 1, 2) | | | -4 | A |
| Diode Forward Voltage | | $V_{SD}$ | $I_F$=-4.0A, $V_{GS}$=0V (Note 1, 2) | | | -1.4 | V |
| Body Diode Reverse Recovery Time | | $t_{rr}$ | $I_F$=-4.0A, $V_{GS}$=0V, di/dt=100A/μs | | 37 | | ns |
| Body Diode Reverse Recovery Charge | | $Q_{rr}$ | | | 61 | | nC |

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

## ■ TEST CIRCUITS AND WAVEFORMS

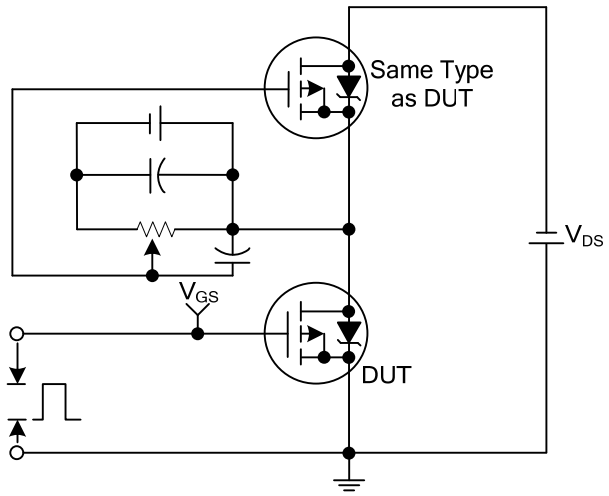



**Peak Diode Recovery dv/dt Test Circuit**

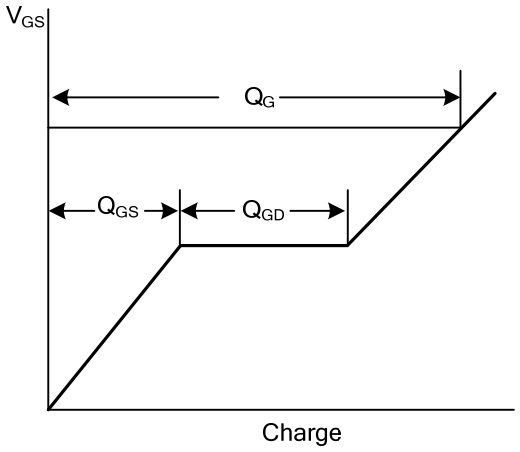



**Peak Diode Recovery dv/dt Waveforms**

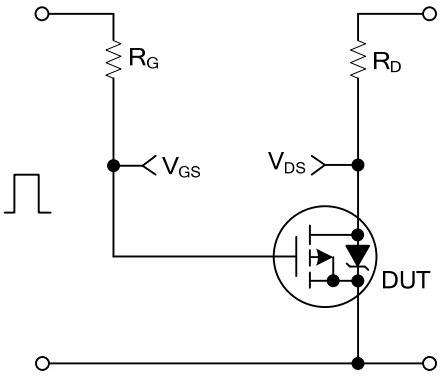
## ■ TEST CIRCUITS AND WAVEFORMS



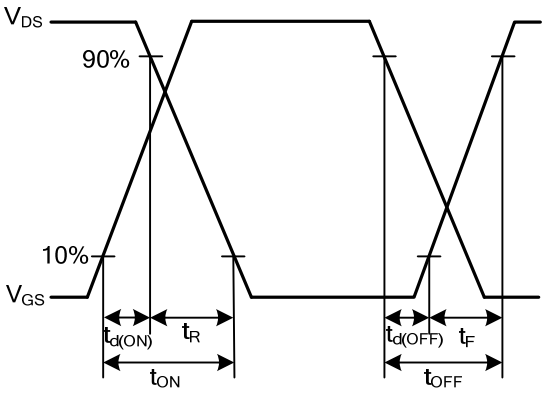

Gate Charge Test Circuit



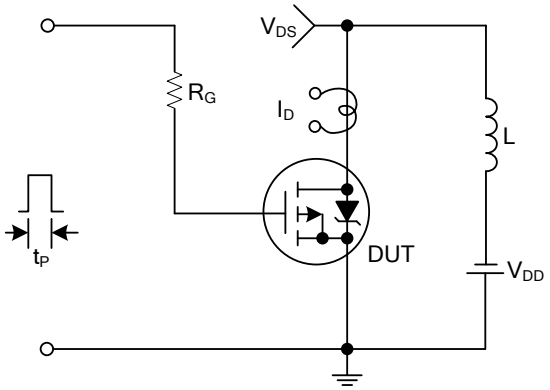

Gate Charge Waveforms



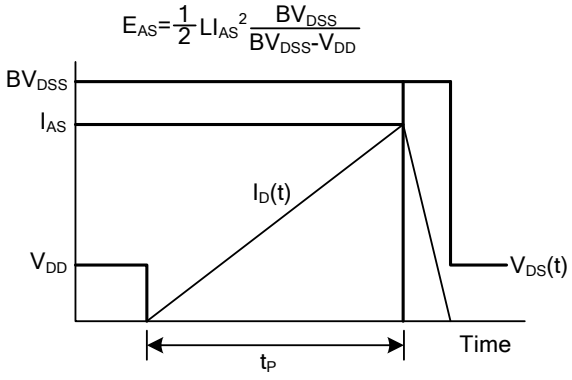

Resistive Switching Test Circuit




Resistive Switching Waveforms




Unclamped Inductive Switching Test Circuit




Unclamped Inductive Switching Waveforms